

# SKM300GM12T4



SEMITRANS® 3

## Fast IGBT4 Modules

SKM300GM12T4

### Features

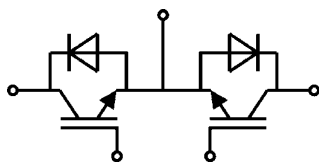
- $V_{CE(sat)}$  with positive temperature coefficient
- High short circuit capability, self limiting to 6 x  $I_{Cnom}$
- Fast & soft inverse CAL diodes
- Large clearance (10 mm) and creepage distances (20 mm)
- Isolated copper baseplate using DBC Technology (Direct Copper Bonding)

### Typical Applications

- Matrix Inverter

### Remarks

- Case temperature limited to  $T_c = 125^\circ\text{C}$  max, recomb.
- $T_{op} = -40 \dots +150^\circ\text{C}$ , product rel. results valid for  $T_j = 150^\circ$



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### Absolute Maximum Ratings

Symbol	Conditions	Values	Unit	
<b>IGBT</b>				
$V_{CES}$		1200	V	
$I_C$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	422	A
		$T_c = 80^\circ\text{C}$	324	A
$I_{Cnom}$		300	A	
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$	900	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150^\circ\text{C}$	10	$\mu\text{s}$
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Inverse diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	353	A
		$T_c = 80^\circ\text{C}$	264	A
$I_{Fnom}$		300	A	
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$	900	A	
$I_{FSM}$	$t_p = 10\text{ ms}$ , $\sin 180^\circ$ , $T_j = 25^\circ\text{C}$	1548	A	
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Module</b>				
$I_{t(RMS)}$		500	A	
$T_{stg}$		-40 ... 125	$^\circ\text{C}$	
$V_{isol}$	AC sinus 50Hz, $t = 1\text{ min}$	4000	V	

### Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
<b>IGBT</b>					
$V_{CE(sat)}$	$I_C = 300\text{ A}$ $V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$	1.85	2.1	V
		$T_j = 150^\circ\text{C}$	2.25	2.45	V
$V_{CE0}$		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	3.5	4.0	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	5.2	5.5	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 12\text{ mA}$	5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
$C_{ies}$	$V_{CE} = 25\text{ V}$		17.6		nF
$C_{oes}$	$V_{GE} = 0\text{ V}$		1.16		nF
$C_{res}$			0.94		nF
$Q_G$	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		1700		nC
$R_{Gint}$	$T_j = 25^\circ\text{C}$		2.5		$\Omega$
$t_{d(on)}$	$V_{CC} = 600\text{ V}$		200		ns
$t_r$	$I_C = 300\text{ A}$ $V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$	44		ns
		$T_j = 150^\circ\text{C}$			
$E_{on}$	$R_{G on} = 1.5\ \Omega$		27		mJ
$t_{d(off)}$	$R_{G off} = 1.5\ \Omega$		450		ns
$t_f$	$di/dt_{on} = 7500\text{ A}/\mu\text{s}$		90		ns
$E_{off}$	$di/dt_{off} = 3350\text{ A}/\mu\text{s}$		29		mJ
$R_{th(j-c)}$	per IGBT			0.11	K/W

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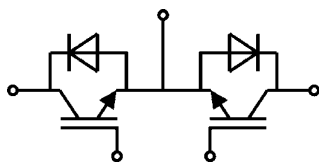
### Typical Applications

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### Remarks

- Case temperature limited to  $T_c = 125^\circ\text{C}$  max, recomm.  
 $T_{op} = -40 \dots +150^\circ\text{C}$ , product rel. results valid for  $T_j = 150^\circ$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverse diode</b>						
$V_F = V_{EC}$	$I_F = 300 \text{ A}$	$T_j = 25^\circ\text{C}$		2.17	2.49	V
	$V_{GE} = 0 \text{ V}$	$T_j = 150^\circ\text{C}$		2.11	2.42	V
	chip					
$V_{F0}$		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
$r_F$		$T_j = 25^\circ\text{C}$		2.9	3.3	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$		4.0	4.4	$\text{m}\Omega$
$I_{RRM}$	$I_F = 300 \text{ A}$	$T_j = 150^\circ\text{C}$		345		A
$Q_{rr}$	$di/dt_{off} = 7300 \text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		54		$\mu\text{C}$
$E_{rr}$	$V_{GE} = \pm 15 \text{ V}$	$T_j = 150^\circ\text{C}$		23		mJ
	$V_{CC} = 600 \text{ V}$					
$R_{th(j-c)}$	per diode				0.17	K/W
<b>Module</b>						
$L_{CE}$				15	20	nH
$R_{CC+EE'}$	terminal-chip	$T_c = 25^\circ\text{C}$		0.25		$\text{m}\Omega$
		$T_c = 125^\circ\text{C}$		0.5		$\text{m}\Omega$
$R_{th(c-s)}$	per module			0.02	0.038	K/W
$M_s$	to heat sink M6		3		5	Nm
$M_t$	to terminals M6		2.5		5	Nm
w					325	g



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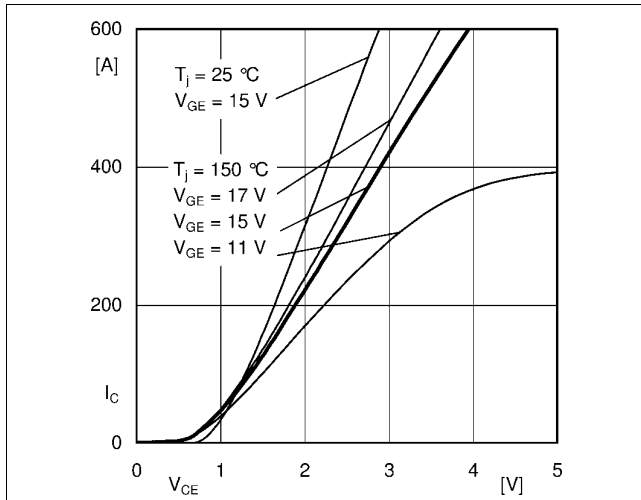


Fig. 1: Typ. output characteristic, inclusive  $R_{CC+EE'}$

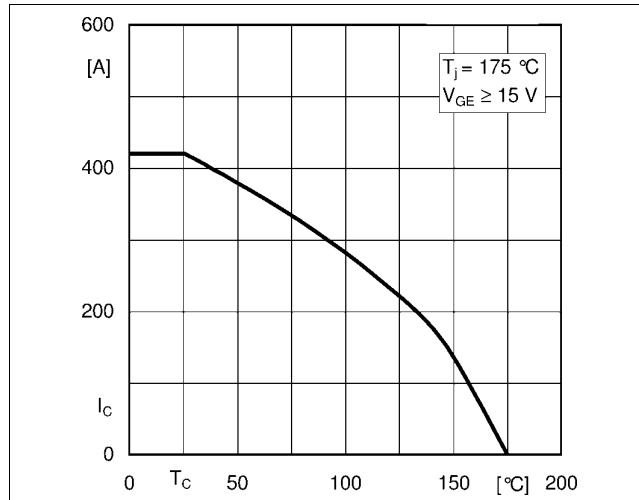


Fig. 2: Rated current vs. temperature  $I_C = f(T_C)$

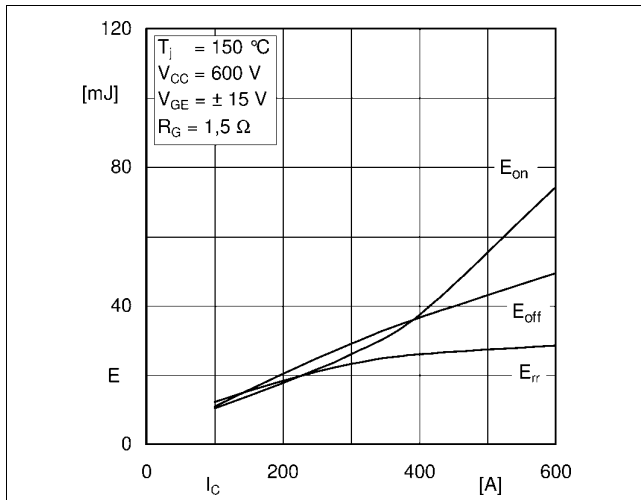


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

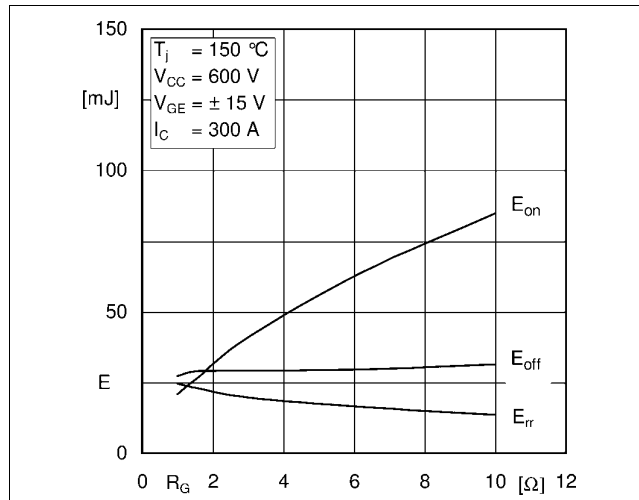


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

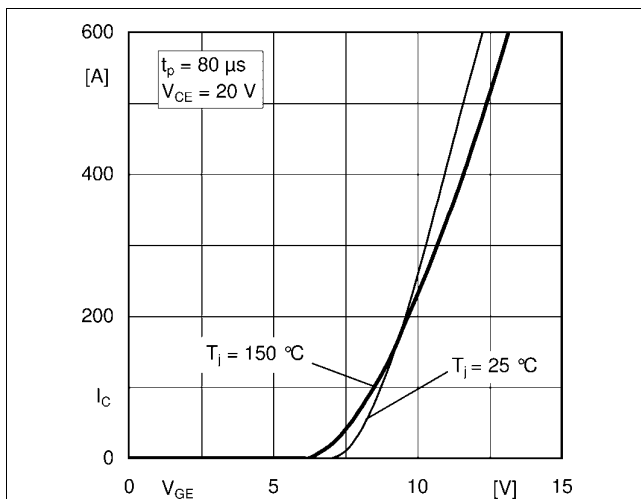


Fig. 5: Typ. transfer characteristic

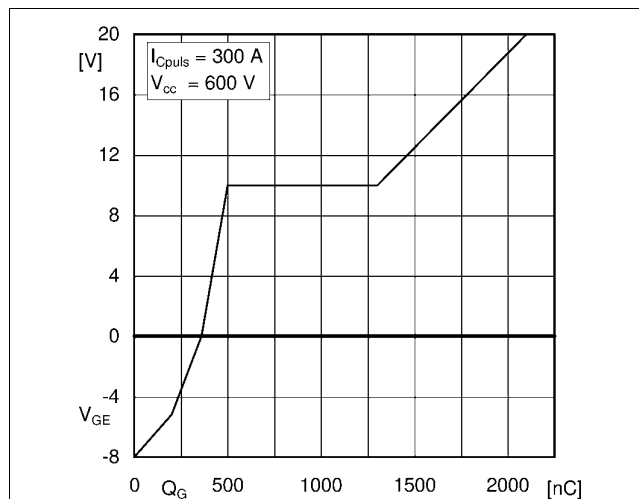


Fig. 6: Typ. gate charge characteristic

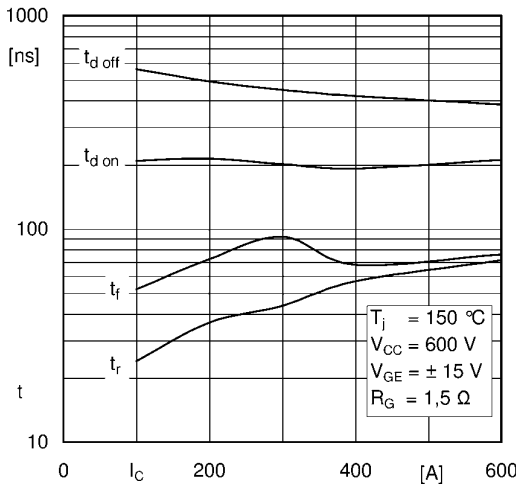


Fig. 7: Typ. switching times vs.  $I_C$

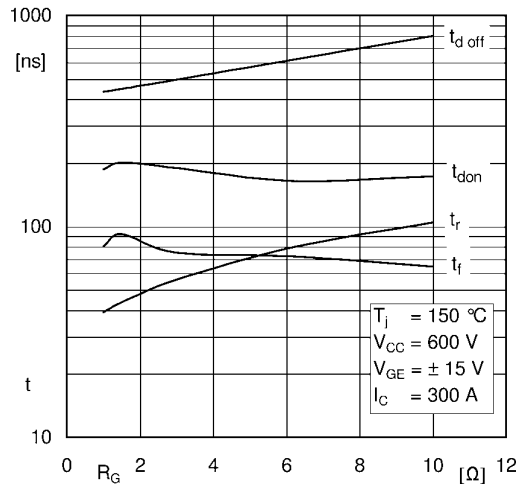


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

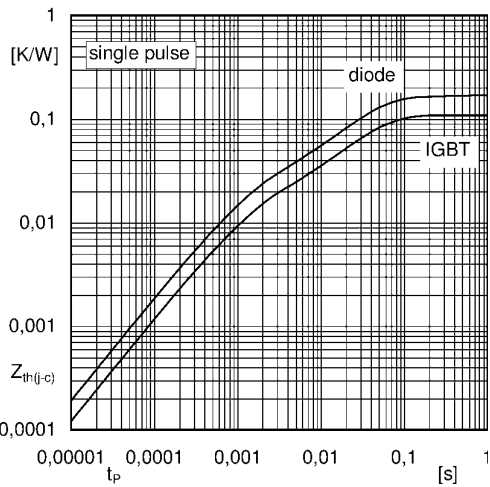


Fig. 9: Transient thermal impedance

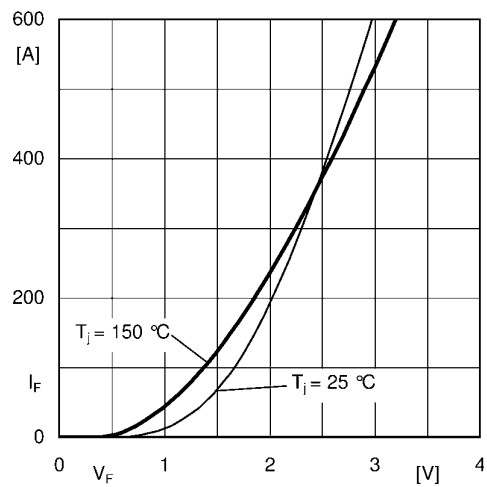


Fig. 10: CAL diode forward characteristic

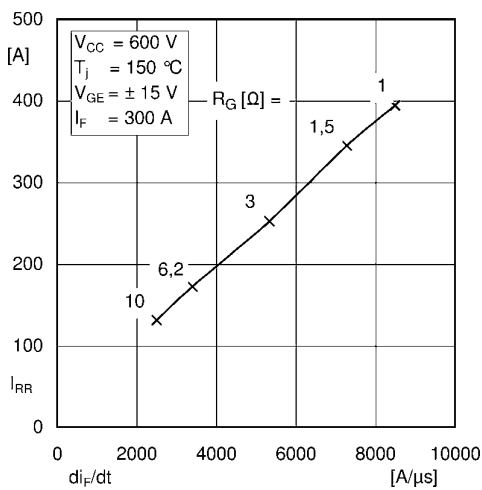


Fig. 11: CAL diode peak reverse recovery current

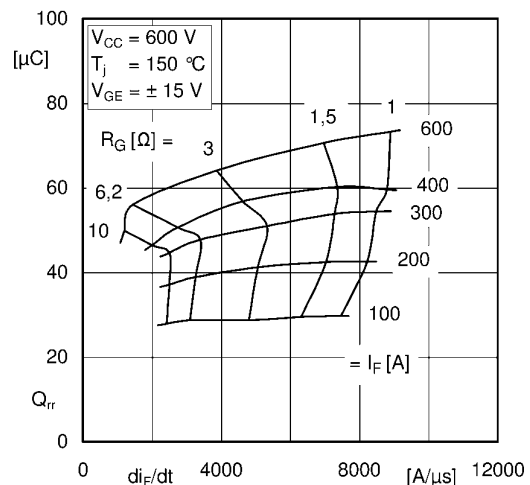
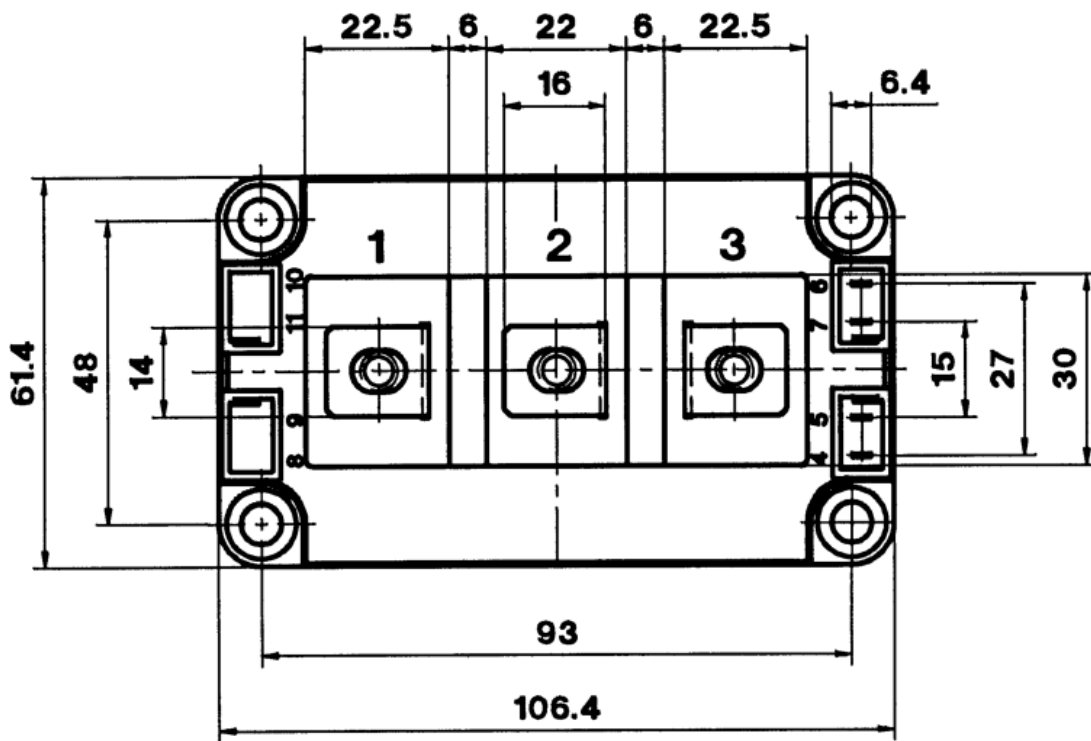
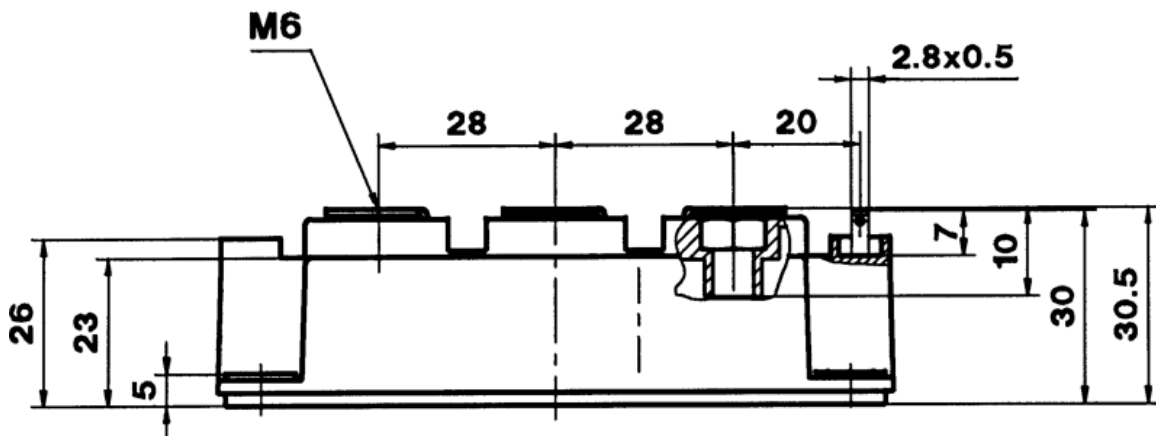
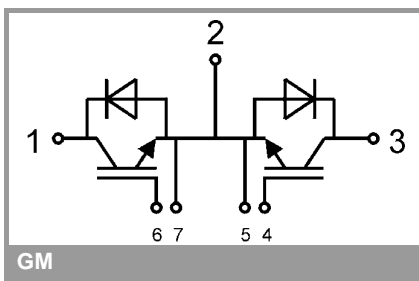


Fig. 12: Typ. CAL diode peak reverse recovery charge



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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